Gas Discharge Tubes(GDT)

3RD-8 Series

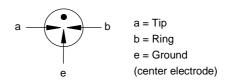
Description

GDT is placed in front of, and in parallel with, sensitive telecom equipment such as power lines, communication lines, signal lines and data transmission lines to help protect them from damage caused by transient surge voltages that may result from lightning strikes and equipment switching operations. These devices do not influence the signal in normal operation. However, in the event of an overvoltage surge, such as a lightning strike, the GDT switches to a low impedance state and diverts the energy away from the sensitive equipment.

Our GDT offer a high level of surge protection, a broad voltage range, low capacitance, and many form factors including new surface mount devices, which makes them suitable for applications such as Main Distribution Frame (MDF) modules, high data-rate telecom applications (e.g. ADSL, VDSL), and surge protection on power lines. Their low capacitance also results in less signal distortion. When used in a coordinated circuit protection solution with PolySwitch devices, they can help equipment manufacturers meet stringent safety regulatory standards.



Electrical symbol



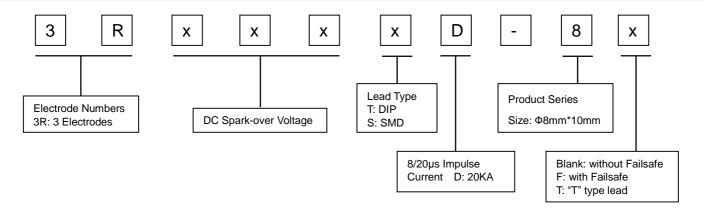
Features

- I Excellent response to fast rising transients
- I Stable breakdown voltage
- I GHz working frequency
- I 8/20µs Impulse current capability: 20KA
- I Non-Radioactive
- I Ultra Low capacitance (<1.5pF)
- I High insulation resistance
- I Lead-free compliant
- I RoHS and REACH compliant
- I UL 497B Recognized: E465335
- I Size: Φ8mm*10mm
- I Storage and operational temperature: -40~+90°C

Applications

- I Communication equipment
- I CATV equipment
- I Data lines
- I Power supplies
- I Telecom SLIC protection
- I Broadband equipment
- I ADSL equipment, including ADSL2+
- I XDSL equipment
- I Satellite and CATV equipment
- I Test equipment
- I Consumer electronics

Part Number Code



Electrical Characteristics

Part Number			DC Spark-over Voltage ^{1) 2) 3} @100V/S	lmp				Life Ratings				
				Spark-over Voltage ³⁾ 100V/µS 1KV/µS		Insulation Resistance	Capacitance @1MHz	Impulse E Cur @8/20	_	AC Discharge Current @50Hz 1S ⁵⁾	Impulse Life @10/1000μS 200A ⁵⁾	
				Max	Max	Min	Max	Nominal ±5 times	Max 1 time	Nominal 5 times	Min	
DIP	SMD	DIP-F	DIP-T	v	V	V	GΩ	pF	KA	KA	Α	Times
3R075TD-8	3R075SD-8	3R075TD-8F	3R075TD-8T	75±20%	500	600	1	1.5	20	25	20	300
3R090TD-8	3R090SD-8	3R090TD-8F	3R090TD-8T	90±20%	500	600	1	1.5	20	25	20	300
3R150TD-8	3R150SD-8	3R150TD-8F	3R150TD-8T	150±20%	500	600	1	1.5	20	25	20	300
3R200TD-8	3R200SD-8	3R200TD-8F	3R200TD-8T	200±20%	600	700	1	1.5	20	25	20	300
3R230TD-8	3R230SD-8	3R230TD-8F	3R230TD-8T	230±20%	600	700	1	1.5	20	25	20	300
3R250TD-8	3R250SD-8	3R250TD-8F	3R250TD-8T	250±20%	600	700	1	1.5	20	25	20	300
3R350TD-8	3R350SD-8	3R350TD-8F	3R350TD-8T	350±20%	800	900	1	1.5	20	25	20	300
3R400TD-8	3R400SD-8	3R400TD-8F	3R400TD-8T	400±20%	850	950	1	1.5	20	25	20	300
3R420TD-8	3R420SD-8	3R420TD-8F	3R420TD-8T	420±20%	850	950	1	1.5	20	25	20	300
3R470TD-8	3R470SD-8	3R470TD-8F	3R470TD-8T	470±20%	900	1000	1	1.5	20	25	20	300
3R600TD-8	3R600SD-8	3R600TD-8F	3R600TD-8T	600±20%	1100	1200	1	1.5	20	25	20	300
3R800TD-8	3R800SD-8	3R800TD-8F	3R800TD-8T	800±20%	1400	1500	1	1.5	20	25	20	300
Glow Volta	ge at 10mA.				~1	60V						
Arc Voltage	e at 1A				~	10V						
Glow to Ar	c transition C	urrent			~	1A						
Operation	and storage				-4	0~+90°C						
Climatic ca	tegory (IEC6	60068-1)			40	0/90/21						
Marking, re	ed negative				X		ominal voltaç					
Weight					S D	IP MD IP-F	~2.10g ~1.85g ~2.35g ~2.15g					
Surface tre	atment						-Nickel Plat -Matte-tin p					

¹⁾ At delivery AQL 0.65 level II, DIN ISO 2859

75V at DC 25V 90V~150V at DC 50V Other at DC 100V

Terms in accordance with ITU-T Rec. K.12, IEC 61643-311, GB/T 9043.

²⁾ In ionized mode

³⁾ Tip or ring electrode to center electrode

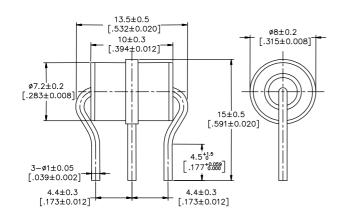
⁴⁾ Insulation Resistance Measuring Voltage:

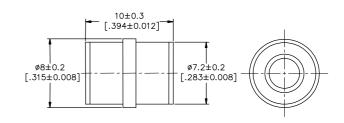
 $^{^{\}rm 5)}$ Total current through center electrode, half value through tip respectively ring electrode.

Dimensions (Unit: mm/inch)

DIP Series (3RxxxTD-8)

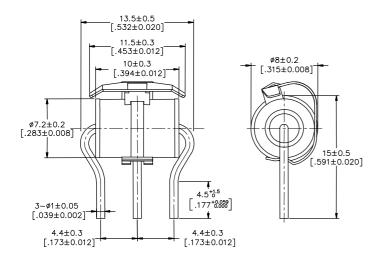
SMD Series (3RxxxSD-8)

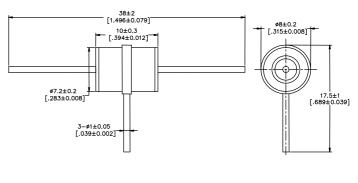




DIP-F Series (3RxxxTD-8F)

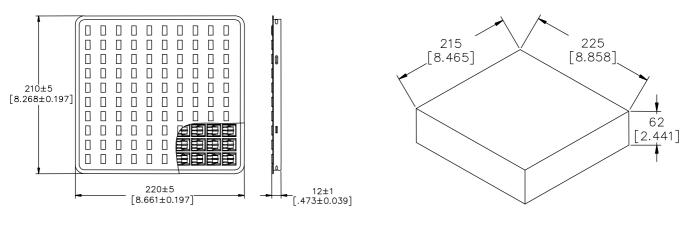
DIP-T Series (3RxxxTD-8T)





Packaging Information (Unit: mm/inch)

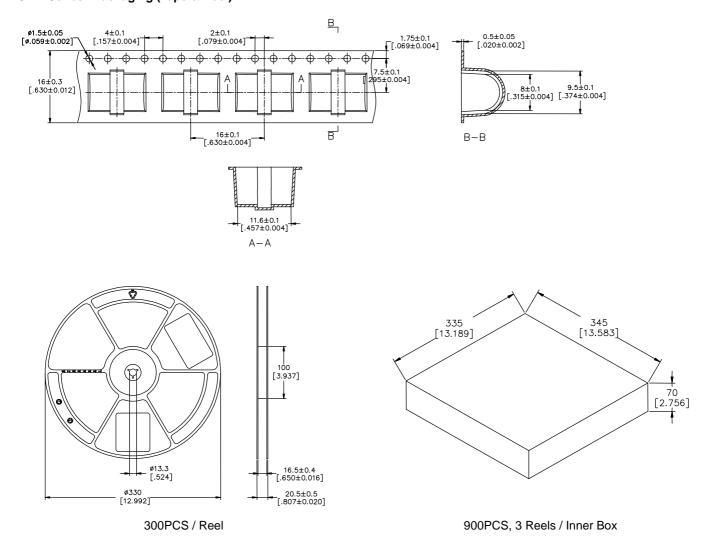
"DIP Series" and "DIP-F Series" Packaging (Bulk)



100PCS/ Plastic Tray

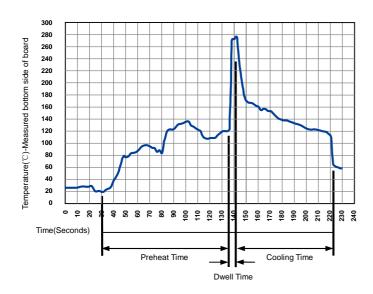
500PCS, 5 Plastic Trays / Inner Box

"SMD Series" Packaging (Tape & Reel)



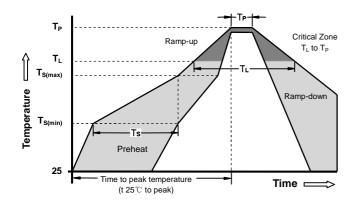
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Soldering Parameters - Wave soldering (Thru-Hole Devices)



Wave Sold	ering Condition	Pb-Free assembly			
	Temperature Min	100°C			
Preheat	Temperature Max	150°C			
	Time (Min to Max)	60-180 Seconds			
Solder Pot	Temperature	280°C Max			
Solder Dw	ell Time	2-5 Seconds			

Soldering Parameters - Reflow Soldering (Surface Mount Devices)



Reflow Co	ndition	Pb - Free			
	-Temperature Min (T _{s(min)})	150°C			
Preheat	-Temperature Max (T _{s(max)})	200°C			
	- Time (min to max) (t _s)	60 -180 Seconds			
Average ra	amp up rate (Liquids Temp	3°C/second max			
T _{S(max)} to T	L - Ramp-up Rate	5°C/second max			
Reflow	- Temperature (T _L) (Liquids)	217°C			
	- Time (min to max) (t _s)	60 -150 Seconds			
Peak Temp	perature (T _P)	260 +0/-5°C			
Time withi	n 5°C of actual peak ıre (t _p)	10 - 30 Seconds			
Ramp-dow	n Rate	6°C/second max			
Time 25°C	to peak Temperature (T _P)	8 minutes Max			
Do not exc	eed	260°C			